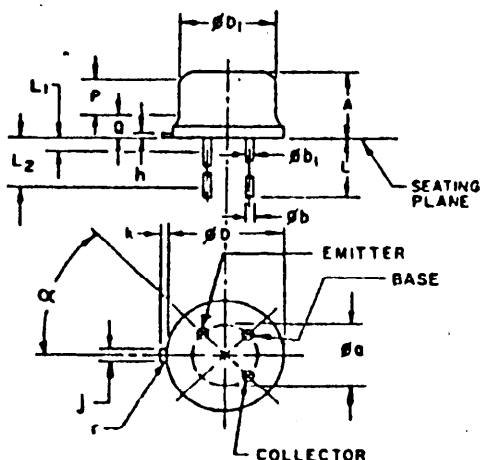


21 August 1972

MILITARY SPECIFICATION

SEMICONDUCTOR DEVICE, TRANSISTOR, PNP, SILICON
TYPE 2N1234

Add attached figure 1 to MIL-S-19500/179A(EL):



DIMENSIONS					NOTES
LTR	INCHES		MILLIMETERS		
	MIN	MAX	MIN	MAX	
A	.240	.260	6.10	6.60	
ØD	200 TP		5.08 TP		6
Øb	.016	.021	.41	.53	7,8
Øb1	.016	.019	.41	.48	7,8
ØD	.335	.370	8.51	9.40	
ØD1	.305	.335	7.75	8.51	
h	.009	.041	.23	1.04	
j	.028	.034	.71	.86	2
k	.020	.045	.74	1.14	3
L	1.500	1.750	38.10	44.45	7,8
L1	---	.050	---	1.27	7,8
L2	.250	---	6.35	---	7,8
P	.100	---	2.54	---	5
Q	---	.050	---	1.27	4
r	---	.010	---	.25	9
α	45 TP		45 TP		6

NOTES:

1. Metric equivalents (to the nearest .01 mm) are given for general information only and are based upon 1 inch = 25.4 mm.
2. Beyond r(radius) maximum, j shall be held for a minimum length of .011(.28 mm).
3. k measured from maximum ØD.
4. Outline in this zone is not controlled.
5. ØD1 shall not vary more than .010(.25 mm) in zone P. This zone is controlled for automatic handling.
6. Leads at gage plane .054 + .001 - .000(1.37 + .03 - .00 mm) below seating plane shall be within .007(.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods or by the gage and gaging procedure shown in figure 2.
7. Øb1 applies between L1 and L2. Øb applies between L2 and L minimum. Diameter is uncontrolled in L1 and beyond L minimum.
8. All three leads.
9. r(radius) applies to both inside corners of tab.

FIGURE 1. Physical dimensions of transistor type 2N1234 (TO-5).Custodian:
Army-ELPreparing Activity:
Army-ELProject No. 5961-A467
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